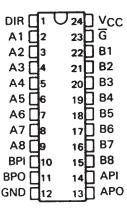
- Bus Transceivers with Inverting Outputs ('HC664) or True Outputs ('HC665)
- Generates a Parity Bit for A Bus and B Bus
- Easily Cascadable
- Internal Active Pull-Ups and Pull-Downs
- High-Current 3-State Outputs Can Drive Up to 15 LSTTL Loads
- Package Options Include Plastic "Small Outline" Packages, Ceramic Chip Carriers, and Standard Plastic and Ceramic 300-mil DIPs
- Dependable Texas Instruments Quality and Reliability

### description

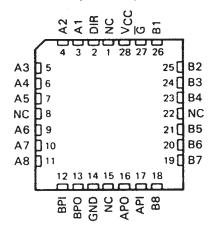
These octal bus transceivers are designed for asynchronous, bidirectional communication between data buses. The devices transmit data from the A Bus to the B Bus or from the B Bus to the A Bus, depending on the level at the direction control input, DIR. The enable input  $\overline{G}$ , can be used to disable the device so that the buses are isolated. These devices will also generate parity outputs, APO and BPO, which reflect the number of high levels at the A Bus and B Bus, respectively, taking into account the parity inputs API and BPI.

The bidirectional I/O ports feature active circuitry on the input stage that, when the output shared by that pin is disabled, will maintain the input in the last state taken by the output. This state will be maintained until changed by the activity on

SN54HC664, SN54HC665 . . . JT PACKAGE SN74HC664, SN74HC665 . . . DW OR NT PACKAGE (TOP VIEW)



SN54HC664, SN54HC665 . . . FK PACKAGE (TOP VIEW)



NC-No internal connection

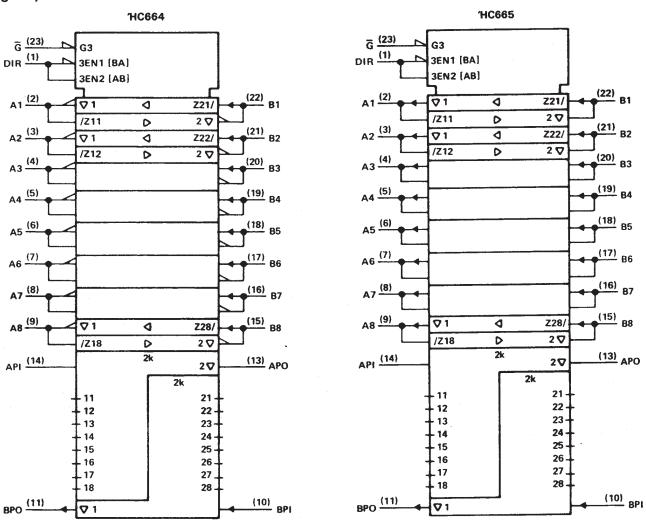
the bus. The advantage of this arrangement is that when all outputs on the bus are disabled, the inputs will be prevented from floating, resulting in minimum power dissipation and minimum susceptibility to noise. This eliminates any need for external pull-up or pull-down resistors. The parity inputs API and BPI have similar circuitry. For futher information, see the Typical Application Data.

The SN54HC664 and SN54HC665 are characterized for operation over the full military temperature range of  $-55\,^{\circ}$ C to 125 °C. The SN74HC664 and SN74HC665 are characterized for operation from  $-40\,^{\circ}$ C to  $85\,^{\circ}$ C.

#### **FUNCTION TABLE**

	TROL	NUMBER OF HIGH	NUMBER OF HIGH	оит	PUTS	OPERATION	
G	UTS DIR	INPUTS ON A BUS AND API	INPUTS ON B BUS AND BPI	APO	вро	<b>НС664</b>	<b>ΉС665</b>
		Х	0, 2, 4, 6, 8	Z	Н	B Data to A Bus	B Data to A Bus
L	L	Х	1, 3, 5, 7, 9	Z	L	b Data to A bus	B Data to A bus
		0, 2, 4, 6, 8	X	Н	Z	A Data to 8 Bus	A Data to B Bus
L	Н	1, 3, 5, 7, 9	X	L	Z	A Data to b bus	A Data to B Bus
Н	×	Х	X	Z	Z	Isolation	Isolation

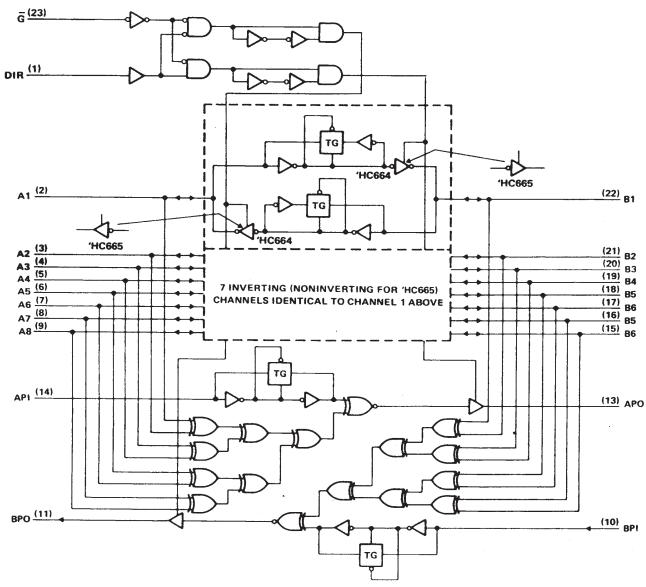
### logic symbols†



<sup>&</sup>lt;sup>†</sup>These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for DW, JT, and NT packages.



### logic diagram (positive logic)



Pin numbers shown are for DW, JT, and NT packages.

### SN54HC664, SN54HC665, SN74HC664, SN74HC665 OCTAL BUS TRANSCEIVERS WITH PARITY

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### absolute maximum ratings over operating free-air temperature range †

Supply voltage, VCC		
Input clamp current, I <sub>IK</sub> ( $V_I < 0$ or $V_I > V_{CC}$ )		
Output clamp current, IOK (VO < 0 or VO > VCC)		± 20 mA
Continuous output current, IO (VO = 0 to VCC)		±35 mA
Continuous current through VCC or GND pins		±70 mA
Lead temperature 1,6 mm (1/16 in) from case for 60 s: FK or JT package		. 300°C
Lead temperature 1,6 mm (1/16 in) from case for 10 s: DW or NT package		. 260°C
Storage temperature range6	35 °C	to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### recommended operating conditions

				N54HC6 N54HC6		2 5 1.5 3.15 4.2			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
Vcc	Supply voltage		2	5	6	2	5	6	٧
		V <sub>CC</sub> = 2 V	1.5			1.5			
$V_{IH}$	High-level input voltage	$V_{CC} = 4.5 V$	3.15			3.15			٧
		V <sub>CC</sub> = 6 V	4.2			4.2		0.3 0.9 1.2	
		V <sub>CC</sub> = 2 V	0		0.3	0		0.3	
VIL	Low-level input voltage	$V_{CC} = 4.5 \text{ V}$	0		0.9	0		0.9	٧
		$V_{CC} = 6 V$	0		1.2	0		1.2	
VĮ	Input voltage		0		Vcc	0		Vcc	V
Vo	Output voltage		0		VCC	0		Vcc	٧
		V <sub>CC</sub> = 2 V	0		1000	0		1000	
t <sub>t</sub>	Input transition (rise and fall) times	$V_{CC} = 4.5 V$	0		500	0		500	ns
•	•	V <sub>CC</sub> = 6 V	0		400	0		0.3 0.9 1.2 VCC VCC 1000	
TA	Operating free-air temperature		- 55		125	-40		85	°C



### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST CONDITIONS	Vcc	т	A = 25	°C	1 -11-0 11	HC664 HC665	SN74H SN74H		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
			2 V	1.9	1.998		1.9		1.9		
VOH		$V_I = V_{IH} \text{ or } V_{IL}, I_{OH} = -20 \mu A$	4.5 V	4.4	4.499		4.4		4.4		
			6 V	5.9	5.999		5.9		5.9		
	All outputs except	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> , I <sub>OH</sub> = -6 mA	4.5 V	3.98	4.30		3.7		3.84		٧
1	APO & BPO	$V_I = V_{IH}$ or $V_{IL}$ , $I_{OH} = -7.8$ mA	6 V	5.48	5.80		5.2		5.34		
Vон	APO or	$V_I = V_{IH}$ or $V_{IL}$ , $t_{OH} = -4$ mA	4.5 V	3.98	4.30		3.7		3.84		
	вро	$V_{I} = V_{IH}$ or $V_{IL}$ , $I_{OH} = -5.2$ mA	6 V	5.48	5.80		5.2		5.34		
		·	2 V		0.002	0.1		0.1		0.1	
VOL		$V_I = V_{IH}$ or $V_{IL}$ , $I_{OL} = 20 \mu A$	4.5 V		0.001	0.1		0.1		0.1	
			6 V		0.001	0.1		0.1		0.1	
	All outputs except	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> , I <sub>OL</sub> = 6 mA	4.5 V		0.17	0.26		0.4		0.33	v
Va	APO & BPO	$V_I = V_{IH}$ or $V_{IL}$ , $I_{OL} = 7.8$ mA	6 V		0.15	0.26		0.4		0.33	
VOL	APO or	VI = VIH or VIL. IOL = 4 mA	4.5 V		0.17	0.26		0.4		0.33	
	BPO	$V_{\parallel} = V_{\parallel} \text{H or } V_{\parallel} \text{L},  \text{lo}_{\parallel} = 5.2 \text{ mA}$	6 V		0.15	0.26		0.4		0.33	
11	G, DIR, API or BPI	VI = VCC or 0	6 V		±0.1	±100	3	1000	±	1000	пА
loz	A or B	$V_O = V_{CC}$ or O	6 V		±0.01	±0.5	_	±10		± 5	μΑ
Icc		$V_I = V_{CC}$ or 0, $I_O = 0$	6 V			8		160		80	μА
C <sub>i</sub> †			2 to 6 V		3	10		10	-	10	рF

<sup>&</sup>lt;sup>†</sup>This parameter, C<sub>i</sub>, does not apply to I/O ports.

## switching characteristics over recommended operating free-air temperature range (unless otherwise noted), C<sub>L</sub> = 50 pF (see Note 1)

	FROM	то		TA	= 25	°C	SN54I	HC664	SN74I	HC664	UNIT	
PARAMETER	(INPUT)	(OUTPUT)	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	190 38 32 290 58 49 195 39 33 320 64 54 320 64 54 75 15	OWIT	
			. 2 V		75	150		225		190		
t <sub>pd</sub>	A or B	B or A	4.5 V		15	30		45		38	ns	
			6 V		13	26		38		32		
	A or B	450	2 V		115	230		345		290		
t <sub>pd</sub>		1	4.5 V		23	46		69		58	กร	
		BPO	6 V		20	39		59		49		
	. 5:	4.00	2 V		77	155		235		195		
t <sub>pd</sub>	API or	ta a l	APO or	4.5 V		15	31		47		39	ns
	BPI	BPO	6 V		13	26		40		33		
			2 V		125	255		385				
t <sub>en</sub>	G or	I Aor B	4.5 V		25	51		77		64	ns	
	DIR		6 V		22	43		65		54		
	5		2 V		125	255		385		320		
<sup>t</sup> dis	Ğ or	A or B	4.5 V		25	51		77		64	ns	
2.0	DIR		6 V		22	43		65	290 58 49 195 39 33 320 64 54 320 64 54 75 15			
			2 V	1	28	60		90		75		
t <sub>t</sub>		Any	4.5 V	-	8	12		18		15	ns	
			6 V		6	10		15		13		

C <sub>pd</sub>	Power dissipation capacitance	No load, TA = 25°C	56 pF typ
Pu	· · · · · · · · · · · · · · · · · · ·		

## switching characteristics over recommended operating free-air temperature range (unless otherwise noted), C<sub>L</sub> = 150 pF (see Note 1)

	FROM	то		T	= 25	°C	SN54	HC664	SN74HC664		UNIT
PARAMETER	(INPUT)	(OUTPUT)	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
			2 V		116	235		355	[	295	
t <sub>pd</sub>	A or B	B or A	4.5 V		23	47		71		59	ns
			6 V		20	41		60		51 395 79 68 300 60	
		100	2 V		157	315		475		395	
t <sub>pd</sub>	A or B	APO or	4.5 V	}	31	63		95	<u> </u>	79	ns
-		BPO	6 V		27	54		81		68	
	4.51	100	2 V		120	240		365		300	-1
<sup>t</sup> pd	API or	APO or	4.5 V		24	48		73		60	
	BPI	BPO	6 V	1	20	41		62		52	
	=		2 V		170	340		515		425	
t <sub>en</sub>	Ğ or	A or B	4.5 V		34	68		103		85	ns
	DIR		6 V		29	58	1	87		73	ns
			2 V		37	210		315		265	
tt		Any	4.5 V		12	42		63		53	ns
-		-	6 V		10	36		53	l	45	Ĺ

NOTE 1: Load circuits and voltage waveforms are shown in Section 1.



## switching characteristics over recommended operating free-air temperature range (unless otherwise noted), C<sub>L</sub> = 50 pF (see Note 1)

	FROM	то		TA	= 25	°C	SN54	HC665	SN74	HC665	UNIT
PARAMETER	(INPUT)	(OUTPUT)	VCC	MIN	TYP	MAX	MIN	MAX	MIN	MAX 175 35 30 290 58 49 195 39 33 320 64 54 320 64 54 75 15	UNIT
			2 V		70	140		210		175	
t <sub>pd</sub>	A or B	B or A	4.5 V		14	28		42		35	ns
PG			6 V		12	24		36		175 35 30 290 58 49 195 39 33 320 64 54 320 64 54 75 15	
	A or B	APO or	2 V		115	230		345		290	
t <sub>pd</sub>			4.5 V		23	46		69		58	ns
ρα		BPO	6 V		20	39		59		49	
			2 V		77	155		235		195	
t <sub>pd</sub>	API or	APO or	4.5 V		15	31		47	1	39	ns
	BPI	BPO	6 V		13	26		40		MAX 175 35 30 290 58 49 195 39 33 320 64 54 320 64 54 75 15	
	-		2 V		125	255		385		320	
t <sub>en</sub>	Ğ or	A or B	4.5 V	1	25	51		47 40 385 77 65		64	ns
CIT	DIR		6 V		22	43		65		175 35 30 290 58 49 195 39 33 320 64 54 75 15	
	*		2 V		125	255		385		290 58 49 195 39 33 320 64 54 320 64 54 75 15	
<sup>t</sup> dis	G or	A or B	4.5 V		25	51	:	77			ns
0.5	DIR		6 V		22	43		65		54	
			2 V		28	60		90		75	
t <sub>t</sub>		Any	4.5 V		8	12		18		15	ns
			6 V		6	10		15		54 75 15 13	
C <sub>pd</sub>	Powe	er dissipation capa	citance		No load	d, T <sub>A</sub> =	25°C		5	6 pF typ	)

C<sub>pd</sub> Power dissipation capacitance No load, T<sub>A</sub> = 25 °C 56 pF typ

# switching characteristics over recommended operating free-air temperature range (unless otherwise noted), C<sub>L</sub> = 150 pF (see Note 1)

	FROM	то		Tρ	= 25	°C	SN54	HC665	SN741	1C665	UNIT
PARAMETER	(INPUT)	(OUTPUT)	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	80 56 49 395 79 68 300 60 52 425 85 73 265 53 45	Oldin
			2 V		112	225		340		280	
t <sub>pd</sub>	A or B	B or A	4.5 V		22	45		68		56	ns
P0			6 V		20	39	-	58		280 56 49 395 79 68 300 60 52 425 85 73 265 53	
			2 V		157	315		475		395	
t <sub>pd</sub>	A or B	APO or	4.5 V		31	63		95		79	ns
Pu		ВРО	6 V		27	54		81		MAX 280 56 49 395 79 68 300 60 52 425 85 73 265 53	
		4.00	2 V		120	240		365		300	
t <sub>pd</sub>	API or		4.5 V	l	24	48	]	73		60	ns
Pu	BPI	BPO	6 V		20	41	l	62		280 56 49 395 79 68 300 60 52 425 85 73 265 53	
	=		2 V		170	340		515		425	
t <sub>en</sub>	Ğ or	A or B	4.5 V		34	68		103		85	ns
···	DIR		6 V		29	58		87		73	
			2 V		37	210		315		265	
tt		Any	4.5 V	1	12	42		63	1	53	ns
			6 V		10	36		53		45	

NOTE 1: Load circuits and voltage waveforms are shown in Section 1.

#### TYPICAL APPLICATION DATA

The unique structure used on the I/O ports and the parity inputs of these devices deserves some special consideration (see Figure 1). Only the input structure is shown. The conventional 3-state output structure associated with each I/O port has been omitted to facilitate understanding.

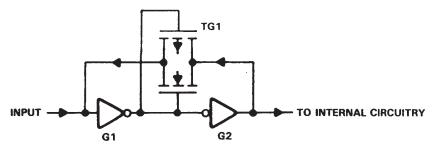


FIGURE 1. INPUT STRUCTURE

The two inverters (G1 and G2) have a transmission gate (TG1) connected in a feedback loop around them. This transmission gate is connected in an unusual fashion, that is, with the gates of both transistors connected to the output of G1. Thus, with the output of G1 at either a high or a low level, one or the other of the transistors will be turned on allowing feedback of the output of G2 to the input of G1. The effect of TG1 is that the input level will be maintained at whatever level existed prior to the bus being disabled or the level currently existing on the bus will be reinforced.

To understand the operation of this input, assume that initially the input is at a low logic level. As the input voltage is raised, TG1 sinks current to attempt to maintain the low level. However, TG1 consists of small geometry transistors and appears resistive as current flows thus allowing the input voltage to rise toward the threshold voltage of G1. When the threshold voltage is reached, G1 changes state causing G2 to change state. G2 then attempts to maintain a high level on the input through TG1. A similar operation occurs when the input voltage is decreased toward the threshold voltage of G1. G2 sources current through TG1 until the threshold is reached.

This characteristic of the input stage has some implications for the input current levels. With the input held at either V<sub>CC</sub> or GND, there is no voltage across TG1 and negligible input current. However, as the input voltage is raised from GND or lowered from V<sub>CC</sub>, the input current rises as the voltage across TG1 increases. The input current continues to rise until it reaches a maximum just as the threshold voltage of G1 is reached.

This configuration provides for minimum power dissipation when the bus is inactive (all outputs on the bus in the high-impedance state) and minimum susceptibility to noise on the bus during this time. The increase in input current may go unnoticed as it only occurs during transitions on the bus. Care must be taken when measuring input currents (e.g., at incoming inspection) to ensure that the input voltage is set to the correct value.

The use of these devices for interfacing to 8-, 16-, 24-bit-wide memory arrays with parity is illustrated in Figures 2, 3 and 4.



#### TYPICAL APPLICATION DATA

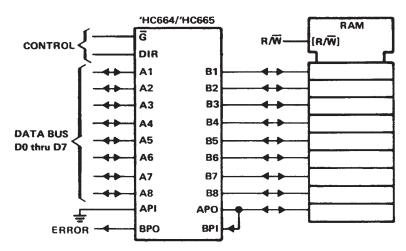


FIGURE 2. 8-BIT-WIDE MEMORY ARRAY WITH PARITY

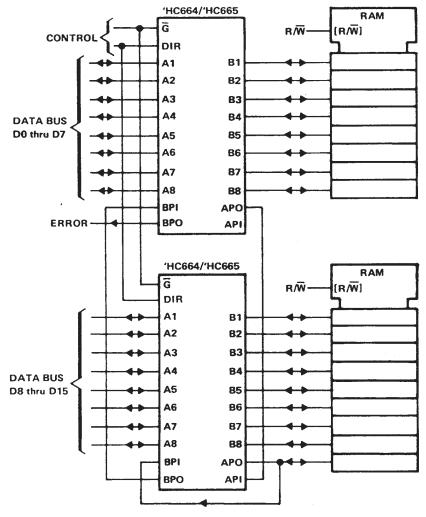


FIGURE 3. 16-BIT-WIDE MEMORY ARRAY WITH PARITY



### TYPICAL APPLICATION DATA

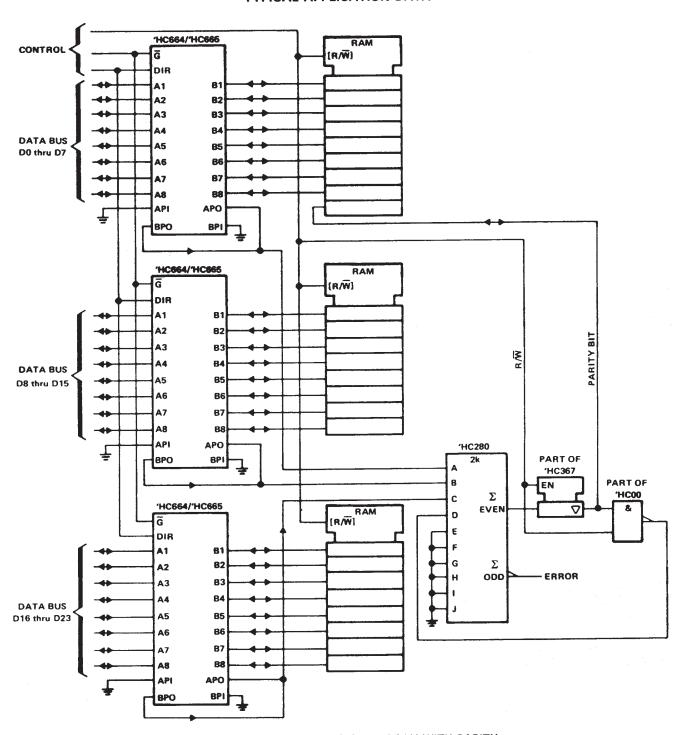


FIGURE 4. 24-BIT-WIDE MEMORY ARRAY WITH PARITY

NOTE: The 'HC280 eliminates ripple carry delays associated with Figures 2 and 3. However, in those two cases the delays are probably too small to be of concern.



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